ESD7951S

ESD Protection Diode

Ultra-Low Capacitance

The ESD7951 is designed to protect voltage sensitive components that require ultra-low capacitance from ESD and transient voltage events. Excellent clamping capability, low capacitance, low leakage, and fast response time, make these parts ideal for ESD protection on designs where board space is at a premium. Because of its low capacitance, it is suited for use in high frequency designs such as USB 2.0 high speed and antenna line applications.

Specification Features:

- Ultra Low Capacitance 0.5 pF
- Low Clamping Voltage
- Small Body Outline Dimensions:
 0.039" x 0.024" (1.00 mm x 0.60 mm)
- Low Body Height: 0.016" (0.4 mm)
- Stand-off Voltage: 5 V
- Low Leakage
- Response Time is Typically < 1.0 ns
- IEC61000-4-2 Level 4 ESD Protection
- SZ Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- This is a Pb-Free Device

Mechanical Characteristics:

CASE: Void-free, transfer-molded, thermosetting plastic

Epoxy Meets UL 94 V-0

LEAD FINISH: 100% Matte Sn (Tin)

MOUNTING POSITION: Any

QUALIFIED MAX REFLOW TEMPERATURE: 260°C

Device Meets MSL 1 Requirements

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
IEC 61000-4-2 (ESD) Contact Air		±8 ±15	kV
Total Power Dissipation on FR-5 Board (Note 1) @ T _A = 25°C	P _D	150	mW
Storage Temperature Range	T _{stg}	-55 to +150	°C
Junction Temperature Range	T_J	-55 to +125	°C
Lead Solder Temperature – Maximum (10 Second Duration)	T_L	260	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

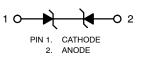
1. $FR-5 = 1.0 \times 0.75 \times 0.62$ in.

See Application Note AND8308/D for further description of survivability specs.



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CASE 514AB

MARKING DIAGRAM



AA M = Specific Device Code

= Date Code

ORDERING INFORMATION

Device	Package	Shipping [†]
ESD7951ST5G,	SOD-923	8000 / Tape &
SZESD7951ST5G	(Pb-Free)	Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

ELECTRICAL CHARACTERISTICS

(T_A = 25°C unless otherwise noted)

Symbol	Parameter
I _{PP}	Maximum Reverse Peak Pulse Current
V _C	Clamping Voltage @ I _{PP}
V _{RWM}	Working Peak Reverse Voltage
I _R	Maximum Reverse Leakage Current @ V _{RWM}
V_{BR}	Breakdown Voltage @ I _T
Ι _Τ	Test Current
I _F	Forward Current
V _F	Forward Voltage @ I _F
P _{pk}	Peak Power Dissipation
С	Capacitance @ V _R = 0 and f = 1.0 MHz

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

		V _{RWM} (V)	I _R (μΑ) @ V _{RWM}	V _{BR} (V) @ I _T (Note 2)	Ι _Τ	С	(pF)	V _C (V) @ I _{PP} = 1 A (Note 3)	v _c
Device*	Device Marking	Max	Max	Min	mA	Тур	Max	Max	Per IEC61000-4-2 (Note 4)
ESD7951ST5G	AA	5.0	1.0	5.4	1.0	0.5	0.9	12.9	Figures 1 and 2 See Below

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

*Includes SZ-prefix devices where applicable.

- 2. V_{BR} is measured with a pulse test current I_T at an ambient temperature of 25°C.
- 3. Surge current waveform per Figure 5.
- 4. For test procedure see Figures 3 and 4 and Application Note AND8307/D.

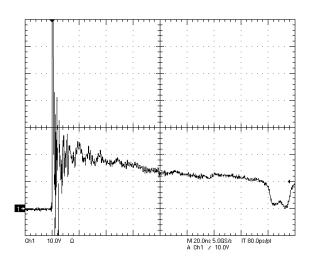


Figure 1. ESD Clamping Voltage Screenshot Positive 8 kV Contact per IEC61000-4-2

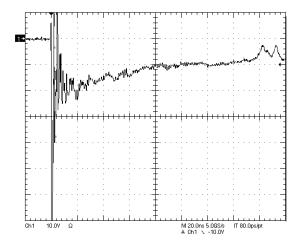


Figure 2. ESD Clamping Voltage Screenshot Negative 8 kV Contact per IEC61000-4-2

V_C V_{BR} V_{RWM} I_R I_R V_{RWM} V_{BR} V_C V

I_R V_{RWM} V_{BR} V_C V

I_R V_{RWM} V_{BR} V_C V

^{*}See Application Note AND8308/D for detailed explanations of datasheet parameters.

IEC 61000-4-2 Spec.

Level	Test Volt- age (kV)	First Peak Current (A)	Current at 30 ns (A)	Current at 60 ns (A)
1	2	7.5	4	2
2	4	15	8	4
3	6	22.5	12	6
4	8	30	16	8

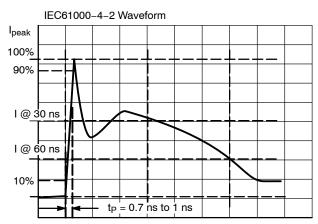


Figure 3. IEC61000-4-2 Spec

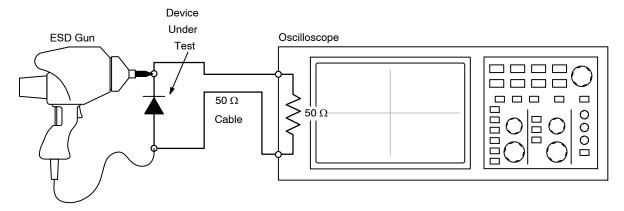


Figure 4. Diagram of ESD Test Setup

The following is taken from Application Note AND8308/D – Interpretation of Datasheet Parameters for ESD Devices.

ESD Voltage Clamping

For sensitive circuit elements it is important to limit the voltage that an IC will be exposed to during an ESD event to as low a voltage as possible. The ESD clamping voltage is the voltage drop across the ESD protection diode during an ESD event per the IEC61000-4-2 waveform. Since the IEC61000-4-2 was written as a pass/fail spec for larger

systems such as cell phones or laptop computers it is not clearly defined in the spec how to specify a clamping voltage at the device level. ON Semiconductor has developed a way to examine the entire voltage waveform across the ESD protection diode over the time domain of an ESD pulse in the form of an oscilloscope screenshot, which can be found on the datasheets for all ESD protection diodes. For more information on how ON Semiconductor creates these screenshots and how to interpret them please refer to AND8307/D.

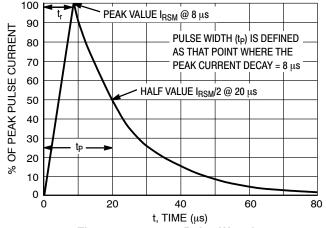


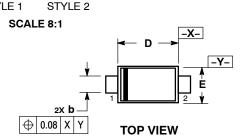
Figure 5. 8 x 20 μs Pulse Waveform

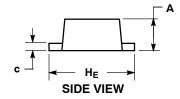


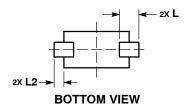


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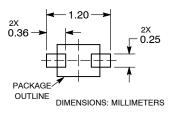
DATE 03 SEP 2020







SOLDERING FOOTPRINT*



See Application Note AND8455/D for more mounting details

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

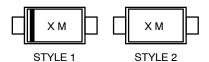
- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
- 2. CONTROLLING DIMENSION: MILLIMETERS.
 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD MAXIMUM LEAD I HICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.

 DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

 DIMENSION L WILL NOT EXCEED 0.30mm.

	MIL	LIMETE	ERS	INCHES		
DIM	MIN	NOM	MAX	MIN	MOM	MAX
Α	0.34	0.37	0.40	0.013	0.015	0.016
b	0.15	0.20	0.25	0.006	800.0	0.010
С	0.07	0.12	0.17	0.003	0.005	0.007
D	0.75	0.80	0.85	0.030	0.031	0.033
Е	0.55	0.60	0.65	0.022	0.024	0.026
HE	0.95	1.00	1.05	0.037	0.039	0.041
L	0.19 REF			0	.007 RE	F
L2	0.05	0.10	0.15	0.002	0.004	0.006

GENERIC MARKING DIAGRAM*



Χ = Specific Device Code

= Date Code

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

STYLE 2: NO POLARITY STYLE 1: PIN 1. CATHODE (POLARITY BAND) 2. ANODE

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DESCRIPTION:	SOD-923, 1.0X0.6X0.37, MAX HEIGHT 0.40		PAGE 1 OF 1		

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